

## Linear Systems replaces discontinued Siliconix SST4119

### The SST4119 is an Ultra-High Input Impedance N-Channel JFET

The SST4119 provides ultra-high input impedance. The device is specified with a 10-pA limit and is ideal for use as a high-impedance sensitive front-end amplifier.

#### SST4119 Benefits:

- Insignificant Signal Loss/Error Voltage with High-Impedance Source
- Low Power Consumption (Battery)
- Maximum Signal Output, Low Noise
- High Sensitivity to Low-Level Signals

#### SST4119 Applications:

- High-Impedance Transducer
- Smoke Detector Input
- Infrared Detector Amplifier
- Precision Test Equipment

#### FEATURES

DIRECT REPLACEMENT FOR SILICONIX SST4119

LOW POWER

$I_{DSS} < 90 \mu A$

MINIMUM CIRCUIT LOADING

$I_{GSS} < 10 pA$

#### ABSOLUTE MAXIMUM RATINGS

@ 25°C (unless otherwise noted)

#### Maximum Temperatures

Storage Temperature

-65°C to +175°C

Operating Junction Temperature

-55°C to +150°C

#### Maximum Power Dissipation

Continuous Power Dissipation

300mW

#### MAXIMUM CURRENT

Gate Current (Note 1)

50mA

#### MAXIMUM VOLTAGES

Gate to Drain or Gate to Source (Note 2)

-40V

#### SST4119 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

| SYMBOL        | CHARACTERISTIC                    | MIN  | TYP. | MAX  | UNITS     | CONDITIONS                                |
|---------------|-----------------------------------|------|------|------|-----------|-------------------------------------------|
| $BV_{GSS}$    | Gate to Source Breakdown Voltage  | -40  | --   | --   | V         | $I_G = -1 \mu A, V_{DS} = 0V$             |
| $V_{GS(off)}$ | Gate to Source Cutoff Voltage     | -2   | --   | -6   | V         | $V_{DS} = 10V, I_D = 1nA$                 |
| $I_{DSS}$     | Gate to Source Saturation Current | 0.20 | --   | 0.60 | mA        | $V_{DS} = 10V, V_{GS} = 0V$               |
| $I_{GSS}$     | Gate Leakage Current              | --   | --   | -10  | pA        | $V_{GS} = -20V, V_{DS} = 0V$              |
|               |                                   | --   | --   | -25  |           | $V_{GS} = -20V, V_{DS} = 0V, 150^\circ C$ |
| $g_{fs}$      | Forward Transconductance (Note 3) | 100  | --   | 330  | $\mu mho$ | $V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$     |
| $g_{os}$      | Output Conductance                | --   | --   | 10   |           |                                           |
| $C_{iss}$     | Input Capacitance                 | --   | --   | 3    | pF        | $V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$     |
| $C_{rss}$     | Reverse Transfer Capacitance      | --   | --   | 1.5  |           |                                           |

#### NOTES

1. Absolute maximum ratings are limiting values above which SST4119 serviceability may be impaired.
2. Due to symmetrical geometry, these units may be operated with source and drain leads interchanged
3. This parameter is measured during a 2ms interval 100ms after power is applied. (Not a JEDEC condition.)

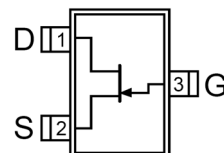
Micross Components Europe

Available Packages:

SOT-23 (Top View)

SST4119 in SOT-23  
SST4119 in bare die.

Please contact Micross for full  
package and die dimensions



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